#### TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

## **TLP127**

# Programmable Controllers DC-Output Module Telecommunication

The TOSHIBA mini flat coupler TLP127 is a small outline coupler, suitable for surface mount assembly.

TLP127 consists of a gallium arsenide infrared emitting diode, optically coupled to a darlington photo transistor with an integral base–emitter resistor, and provides  $300V\ VCEO$ .

- Collector-emitter voltage: 300 V (min.)
- Current transfer ratio: 1000% (min.)
- Isolation voltage: 2500Vrms (min.)
- UL recognized: UL1577, file no. E67349
- BSI approved: BS EN60065:2002, certificate no.8927 BS EN60950-1:2002, certificate no.8928

Unit in mm

6 4
7 7.0 ± 0.4

1 3

3.6 ± 0.2

0.4

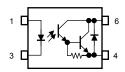
0.5 MIN.

11-4C1

TOSHIBA 11-4C1

Weight: 0.09 g

### Pin Configurations (top view)



- 1 : ANODE
- 3 : CATHODE
- 4 : EMITTER
- 6 : COLLECTOR

### Absolute Maximum Ratings (Ta = 25°C)

|  | Characteristic                                   | Symbol               | Rating                      | Unit    |
|--|--|----------------------|-----------------------------|---------|
|  | Forward current                                  | lF                   | 50                          | mA      |
| ED   | Forward current derating                         | ΔI <sub>F</sub> / °C | –0.7 (Ta ≥ 53°C)            | mA / °C |
|  | Pulse forward current                            | IFP                  | 1 (100µs pulse, 100pps)     | Α       |
|  | Reverse voltage                                  | V <sub>R</sub>       | 5                           | V       |
|  | Junction temperature                             | Tj                   | 125                         | °C      |
|  | Collector-emitter voltage                        | V <sub>CEO</sub>     | 300                         | V       |
|  | Emitter-collector voltage                        | V <sub>ECO</sub>     | 0.3                         | V       |
| tor  | Collector current                                | IC                   | 150                         | mA      |
| Detector   | Collector power dissipation                      | PC                   | 150                         | mW      |
|  | Collector power dissipation derating (Ta ≥ 25°C) | ΔP <sub>C</sub> / °C | -1.5                        | mW / °C |
|  | Junction temperature                             | Tj                   | 125                         | °C      |
| Storage temperature range                            |  | T <sub>stg</sub>     | -55~125                     | °C      |
| Operating temperature range                          |  | T <sub>opr</sub>     | -55~100                     | °C      |
| Lead soldering temperature                           |  | T <sub>sol</sub>     | 260 (10s)                   | °C      |
| Total package power dissipation                      |  | P <sub>T</sub>       | 200                         | mW      |
| Total package power dissipation derating (Ta ≥ 25°C) |  | ΔP <sub>T</sub> / °C | -2.0                        | mW / °C |
| Isolation voltage (Note 1)                           |  | BVS                  | 2500 (AC, 1min., R.H.≤ 60%) | Vrms    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: Pins 1, 3 shorted together and pins 4, 6 shorted together.

## Individual Electrical Characteristics (Ta = 25°C)

|          | Characteristic                          | Symbol                | Test Condition                     | Min. | Тур. | Max. | Unit |
|----------|---|-----------------------|------------------------------------|------|------|------|------|
|          | Forward voltage                         | V <sub>F</sub>        | I <sub>F</sub> = 10 mA             | 1.0  | 1.15 | 1.3  | V    |
| LED      | Reverse current                         | I <sub>R</sub>        | VR = 5V                            | _    | _    | 10   | μA   |
|          | Capacitance                             | C <sub>T</sub>        | V = 0, f = 1 MHz                   | _    | 30   | _    | pF   |
| Detector | Collector–emitter breakdown voltage     | V <sub>(BR)</sub> CEO | I <sub>C</sub> = 0.1 mA            | 300  | _    | -    | V    |
|          | Emitter-collector breakdown voltage     | V <sub>(BR)</sub> ECO | I <sub>E</sub> = 0.1 mA            | 0.3  | _    | _    | V    |
|          | Collector dark current I <sub>CEO</sub> | lana                  | V <sub>CE</sub> = 200 V            | _    | 10   | 200  | nA   |
|          |   | ICEO                  | V <sub>CE</sub> = 200 V, Ta = 85°C | _    | _    | 20   | μA   |
|          | Capacitance collector to emitter        | C <sub>CE</sub>       | V = 0, f = 1 MHz                   |      | 12   |      | pF   |

## **Coupled Electrical Characteristics (Ta = 25°C)**

| Characteristic         | Symbol                                | Test Condition                                  | MIn. | Тур. | Max. | Unit |
|------------------------|---------------------------------------|---|------|------|------|------|
| Current transfer ratio | I <sub>C</sub> / I <sub>F</sub>       | I <sub>F</sub> = 1mA, V <sub>CE</sub> = 1 V     | 1000 | 4000 | _    | %    |
| Saturated CTR          | I <sub>C</sub> / I <sub>F (sat)</sub> | I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 1 V   | 500  | _    | _    | %    |
| Collector-emitter      | V0= ( ))                              | I <sub>C</sub> = 10 mA, I <sub>F</sub> = 1 mA   | _    | _    | 1.0  | V    |
| saturation voltage     | V <sub>CE</sub> (sat)                 | I <sub>C</sub> = 100 mA, I <sub>F</sub> = 10 mA | 0.3  | _    | 1.2  | V    |

## **Isolation Characteristics (Ta = 25°C)**

| Characteristic                | Symbol         | Test Condition                    | Min.               | Тур.             | Max. | Unit             |
|-------------------------------|----------------|-----------------------------------|--------------------|------------------|------|------------------|
| Capacitance (input to output) | CS             | V <sub>S</sub> = 0, f = 1 MHz     | -                  | 0.8              | _    | pF               |
| Isolation resistance          | R <sub>S</sub> | V <sub>S</sub> = 500 V, R.H.≤ 60% | 5×10 <sup>10</sup> | 10 <sup>14</sup> | _    | Ω                |
|                               |                | AC, 1 minute                      | 2500               | _                | _    | V                |
| Isolation voltage             | $BV_S$         | AC, 1 second, in oil              | _                  | 5000             | _    | V <sub>rms</sub> |
|                               |                | DC, 1 minute, in oil              | _                  | 5000             | _    | $V_{dc}$         |

## **Switching Characteristics (Ta = 25°C)**

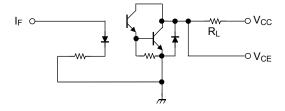
| Characteristic | Symbol           | Test Condition  | Min. | Тур. | Max. | Unit |
|----------------|------------------|---|------|------|------|------|
| Rise time      | t <sub>r</sub>   |   | _    | 40   | _    | μs   |
| Fall time      | t <sub>f</sub>   | V <sub>CC</sub> = 10 V, I <sub>C</sub> = 10 mA                          | _    | 15   | _    |      |
| Turn-on time   | t <sub>on</sub>  | R <sub>L</sub> = 100 Ω  | _    | 50   | _    |      |
| Turn-off time  | t <sub>off</sub> |   | _    | 15   | _    |      |
| Turn-on time   | t <sub>ON</sub>  |   | _    | 5    | _    |      |
| Storage time   | ts               | $R_L = 180 \Omega$ (Fig.1) $V_{CC} = 10 \text{ V}, I_F = 16 \text{ mA}$ | _    | 40   | _    | μs   |
| Turn-off time  | toff             |   | _    | 80   | _    |      |

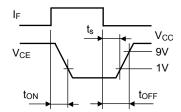
## **Recommended Operating Conditions**

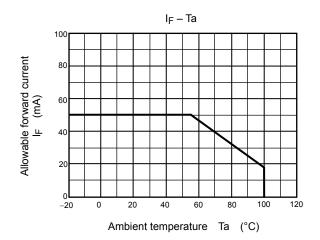
| Characteristic        | Symbol           | Min. | Тур. | Max. | Unit |
|-----------------------|------------------|------|------|------|------|
| Supply voltage        | V <sub>CC</sub>  | _    | _    | 200  | V    |
| Forward current       | lF               | _    | 16   | 25   | mA   |
| Collector current     | IC               | _    | _    | 120  | mA   |
| Operating temperature | T <sub>opr</sub> | -25  | _    | 85   | °C   |

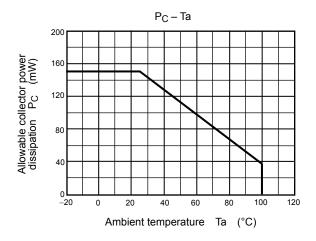
Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

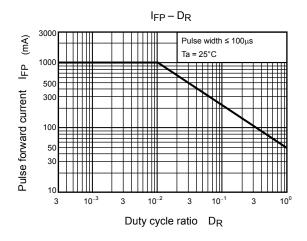
Fig. 1 Switching time test circuit

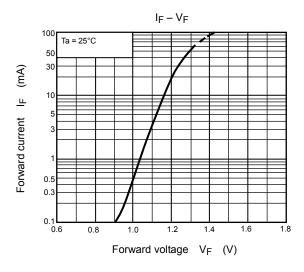


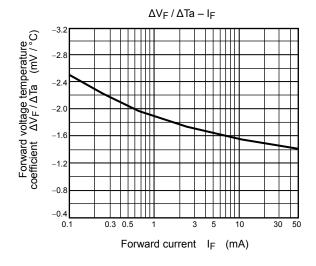


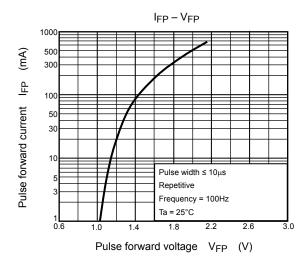


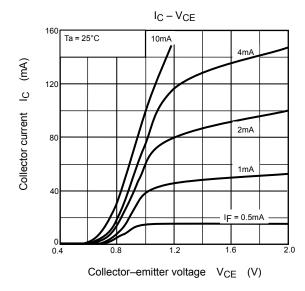


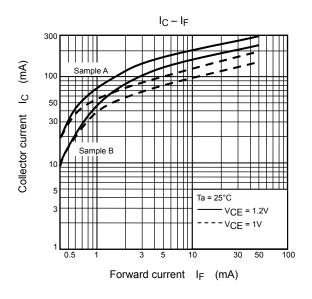


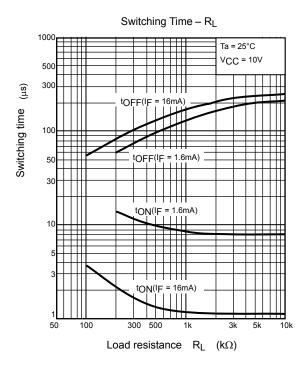


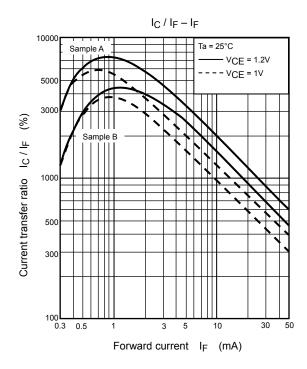


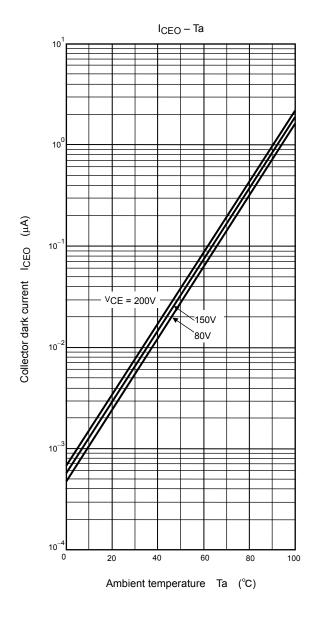


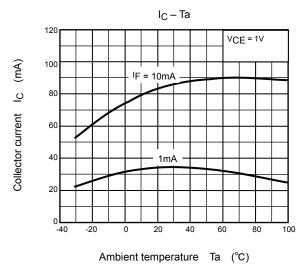


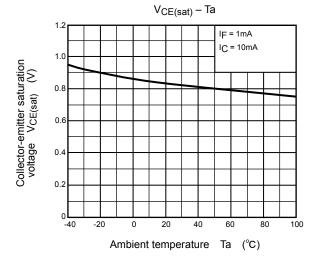












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#### **RESTRICTIONS ON PRODUCT USE**

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